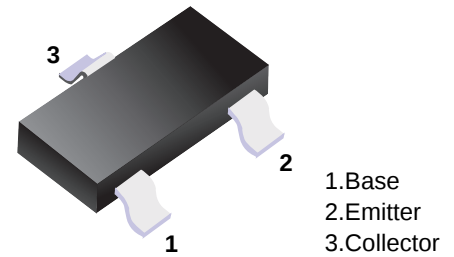


S9015

PNP Transistors

Features

- Complementary to S9014



Simplified outline(SOT-23)

Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	-50	V
Collector-Emitter Voltage	V _{CEO}	-45	V
Emitter-Base Voltage	V _{EB0}	-5	V
Collector Current -Continuous	I _C	-0.1	A
Collector Power Dissipation	P _C	0.2	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 to 150	°C

Electrical Characteristics Ta = 25°C

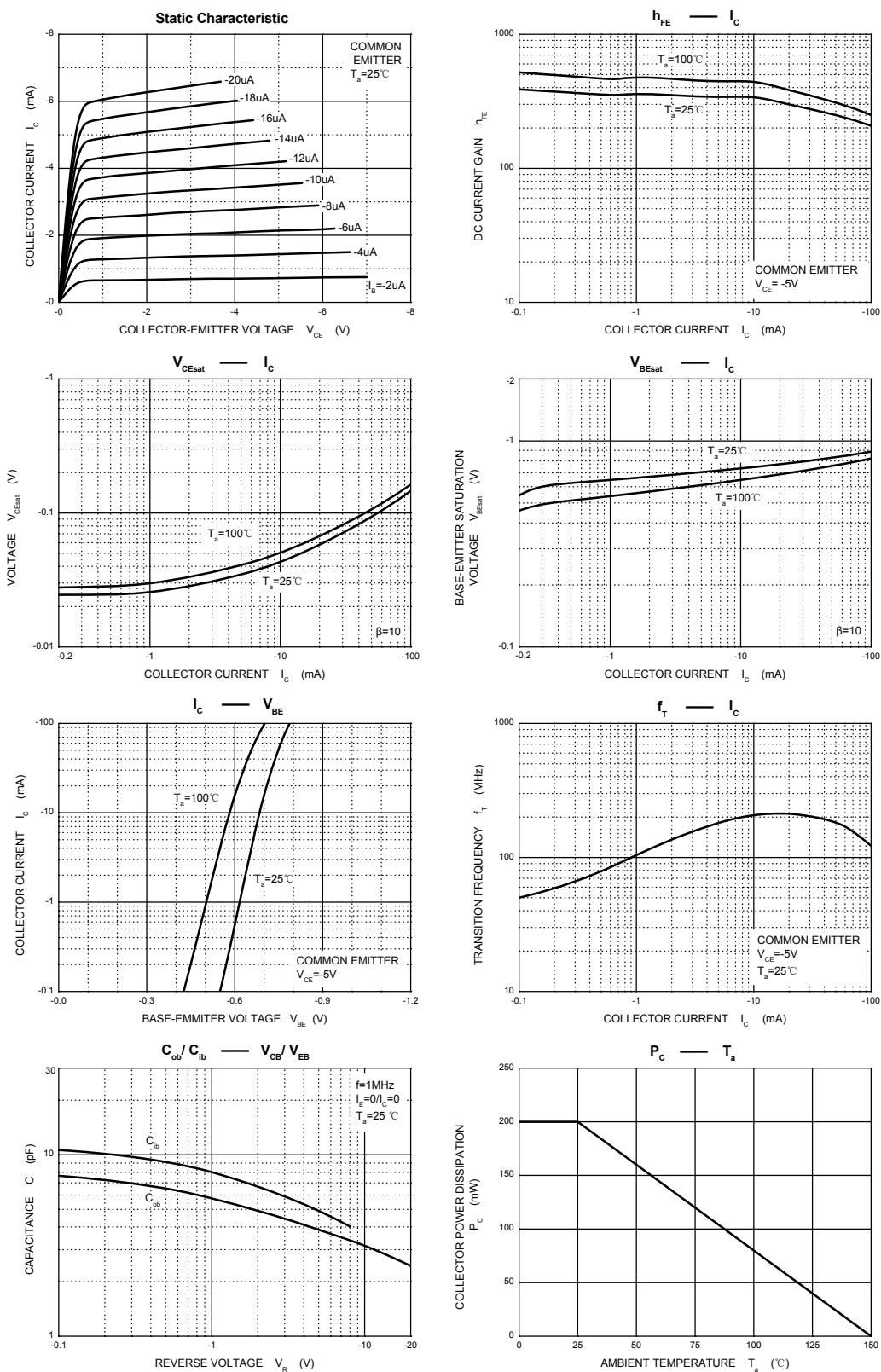
Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{CB0}	I _C =-100uA, I _E =0	-50			V
Collector-emitter breakdown voltage	V _{CEO}	I _C =-1mA, I _B =0	-45			V
Emitter-base Breakdown voltage	V _{EB0}	I _E =-100 uA, I _C =0	-5			V
Collector cutoff current	I _{CBO}	V _{CB} =-50V, I _E =0			-0.1	μ A
Emitter cutoff current	I _{EB0}	V _{EB} =-5V, I _C =0			-0.1	μ A
DC current gain	h _{FE}	V _{CE} =-5V, I _C =-1mA	200		1000	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-100mA, I _B =-10mA			-0.3	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-100mA, I _B =-10mA			-1	V
Transition frequency	f _T	V _{CE} =-5V, I _C =-10mA, f=30MHZ	150			MHz

hFE Classification

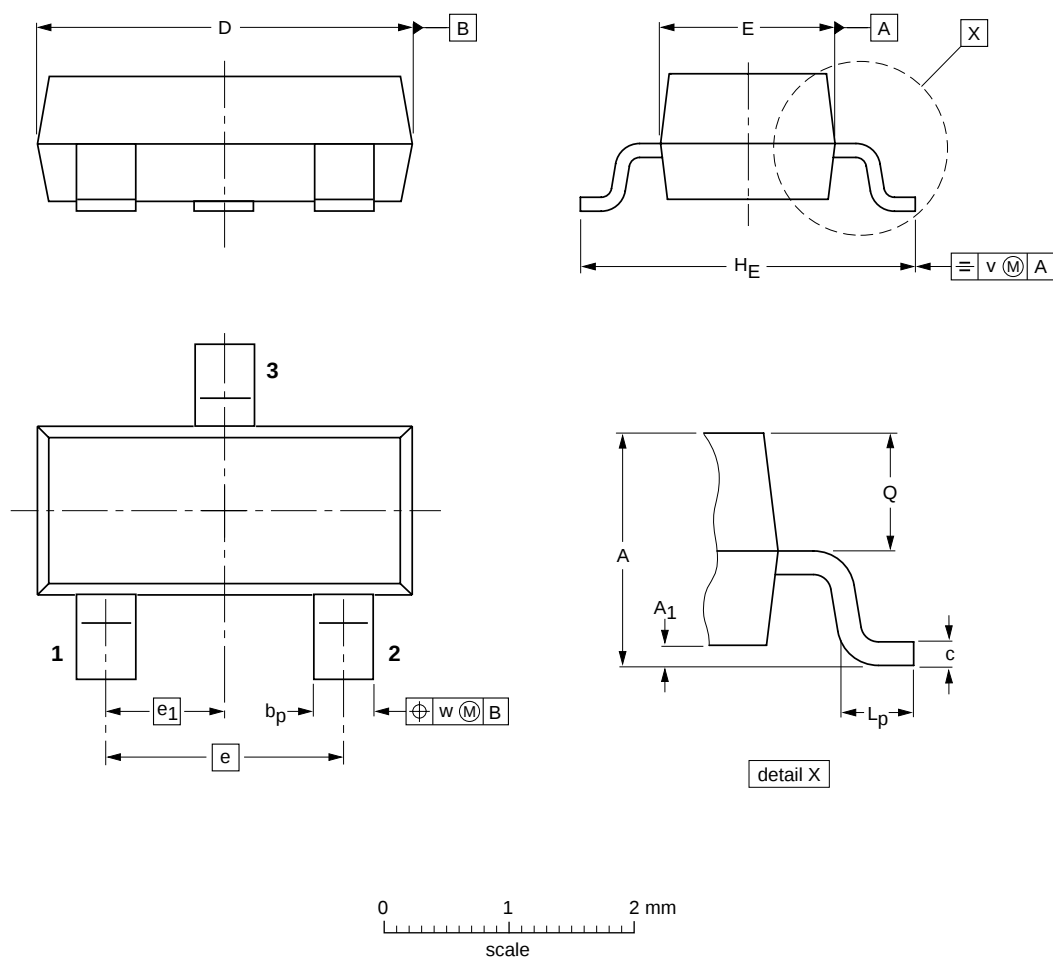
Type	S9015-L	S9015-H
Range	200-450	450-1000
Marking	M6	

S9015

Typical Characteristics



■ SOT-23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1